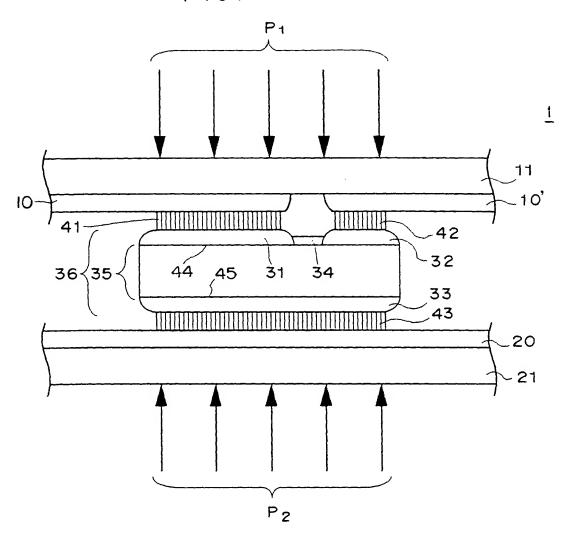
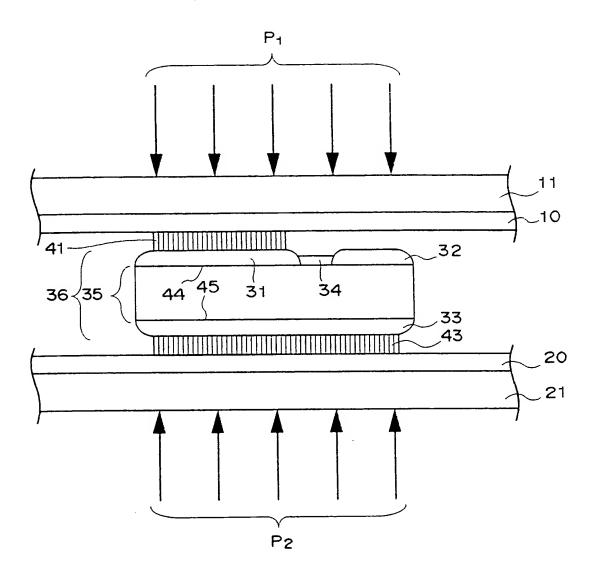
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FIG.I

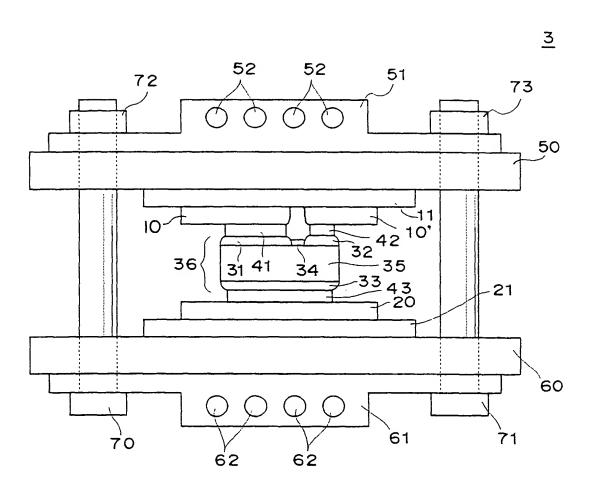


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F I G . 2

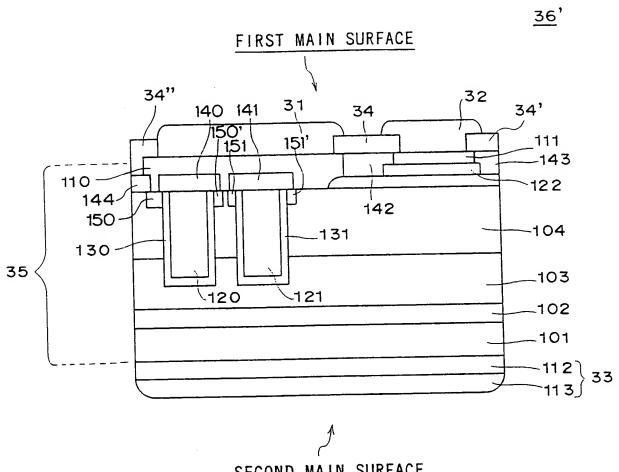


F1G. 3



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FIG. 4



SECOND MAIN SURFACE

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MANUFACTURING PROCESS OF TRENCH IGBT ELEMENT

